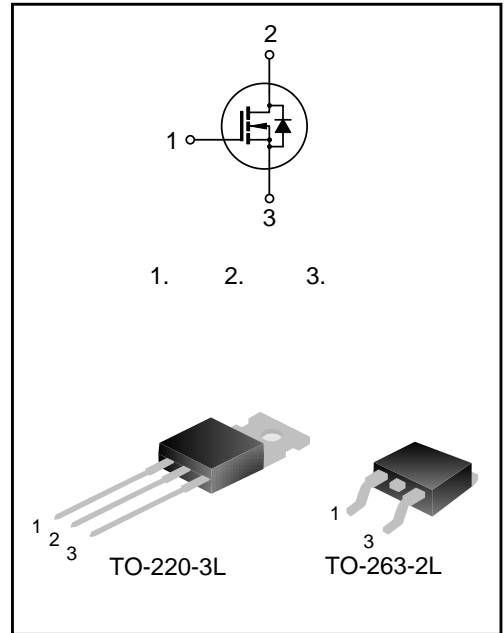




SVG095R0NT(S) N MOS
LVMOS

120A 90V $R_{DS(on)} = 4.4m @ V_{GS}=10V$

dv/dt



SVG095R0NT	TO-220-3L	095R0NT		
SVG095R0NS	TO-263-2L	095R0NS		

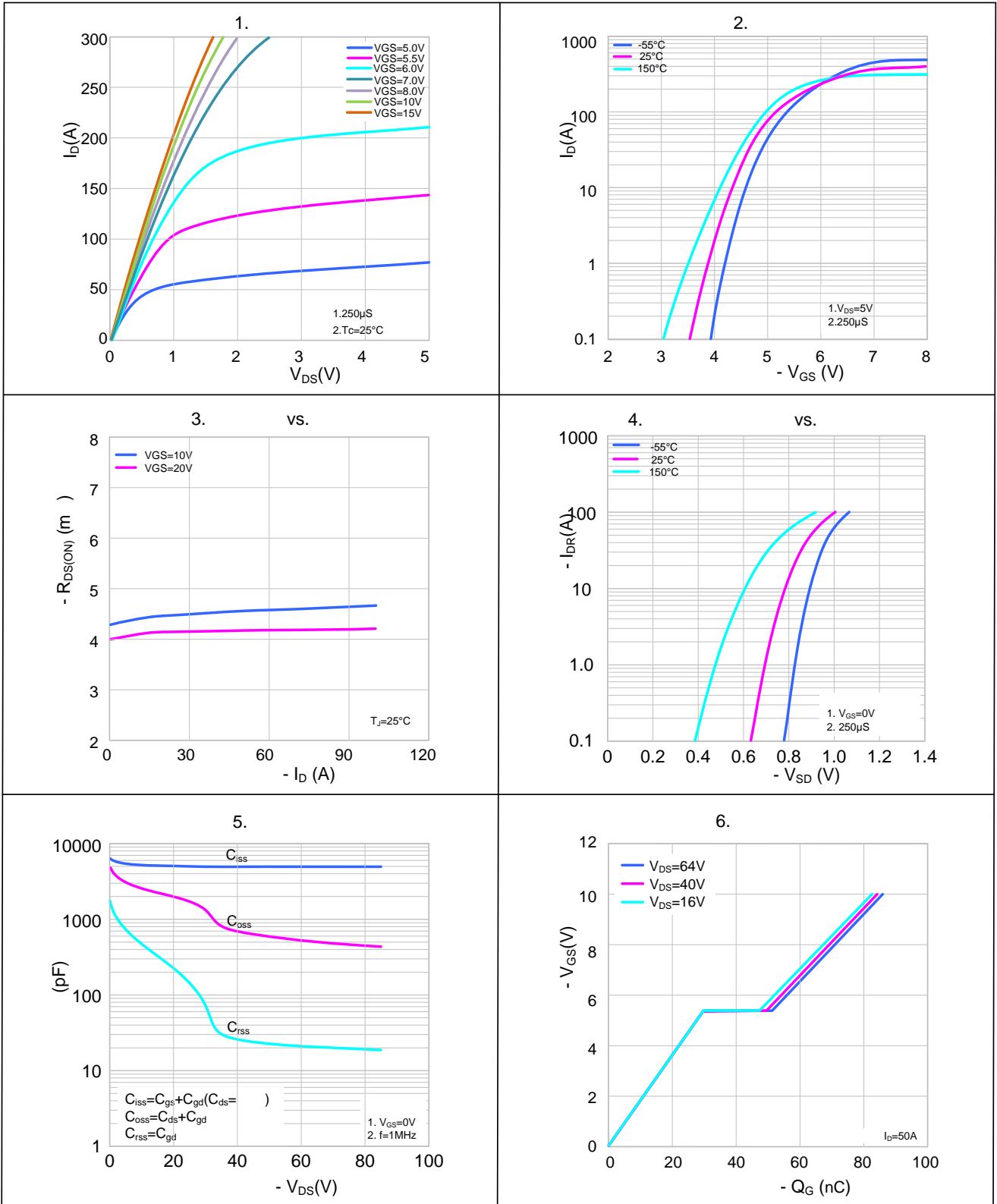


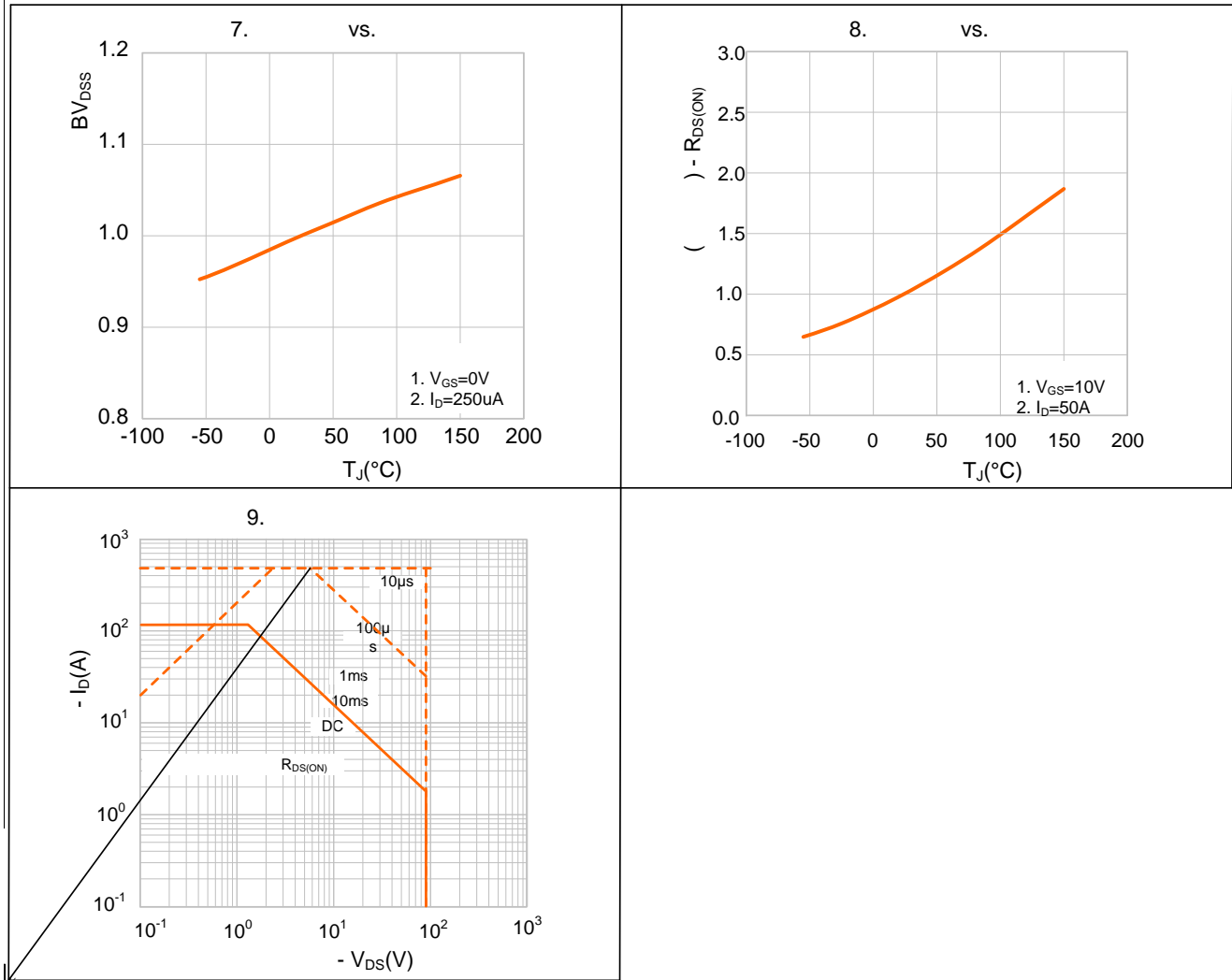
	V_{DS}	90	V
	V_{GS}	± 20	V
$T_C=25^\circ\text{C}$	I_D	147	A

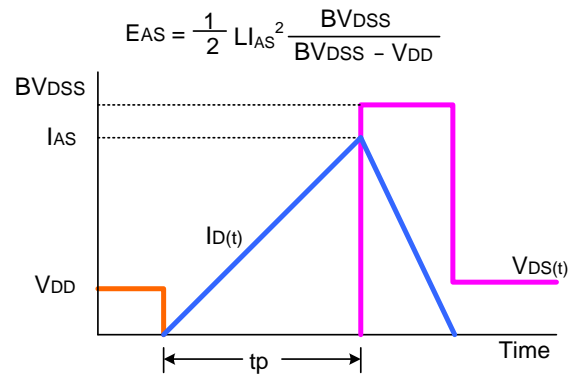
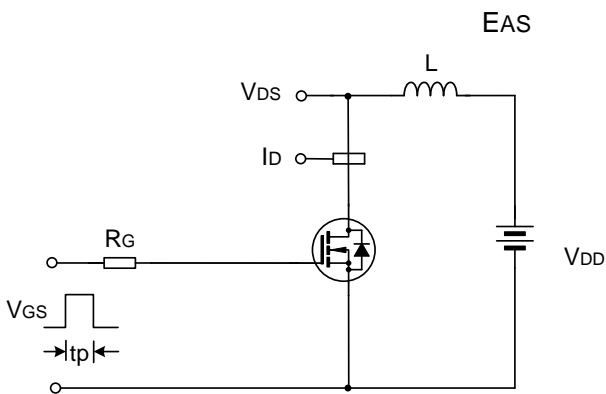
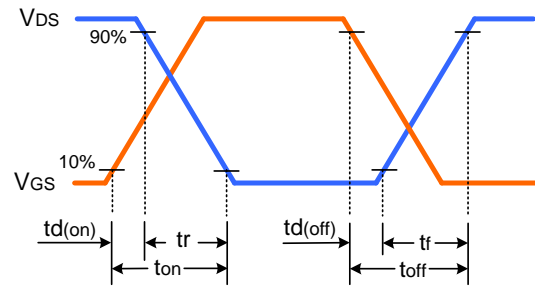
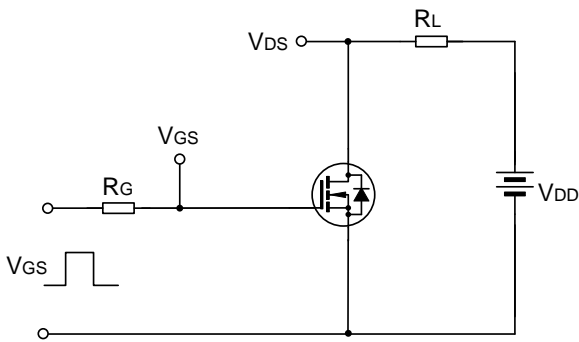
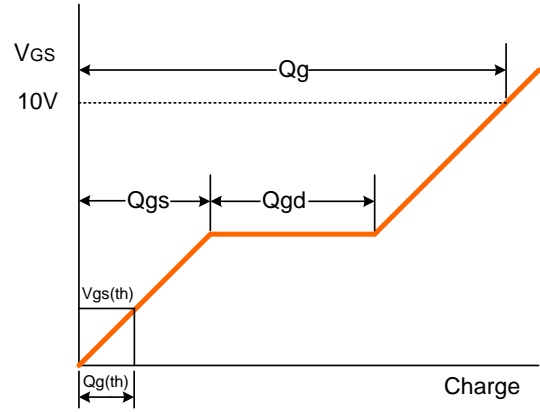
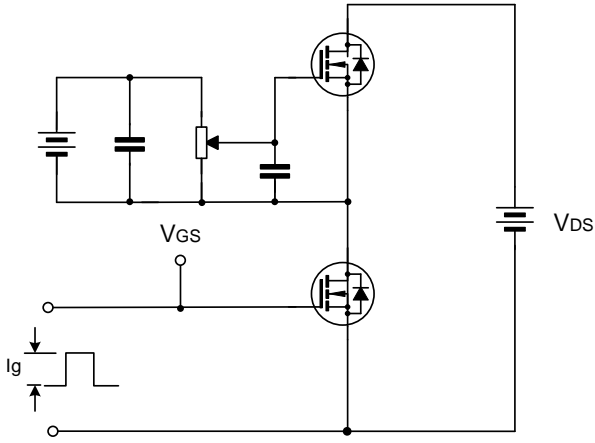


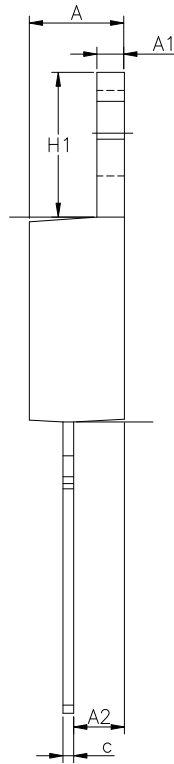
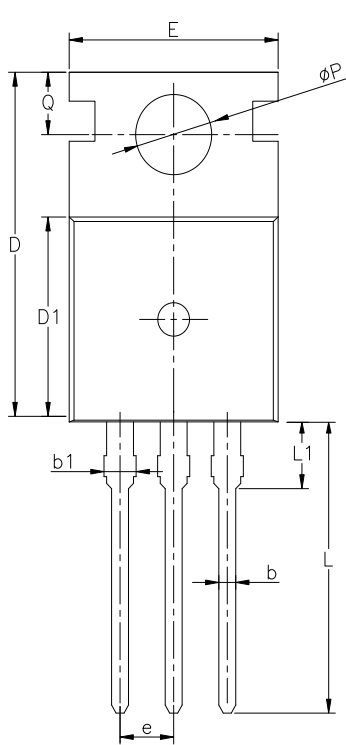
	I_S	MOS	--	--	120	A
	I_{SM}	P-N	--	--	480	
-	V_{SD}	$I_S=50A, V_{GS}=0V$	--	--	1.4	V
	T_{rr}	$I_S=20A, V_{GS}=0V,$	--	66	--	ns
	Q_{rr}	$dI/dt=100A/\mu s$ (2)	--	0.14	--	μC

1. $L=0.5mH$ $I_{AS}=42A$ $V_{DD}=72V$ $R_G=25$ $T_J=25 C$
- 2.
- 3.

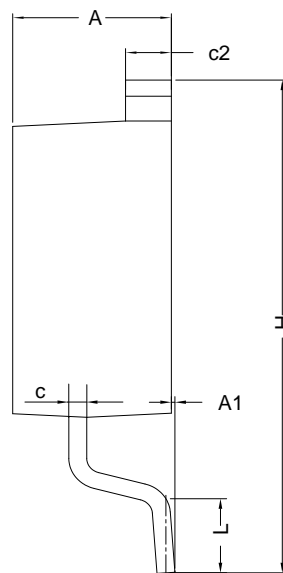
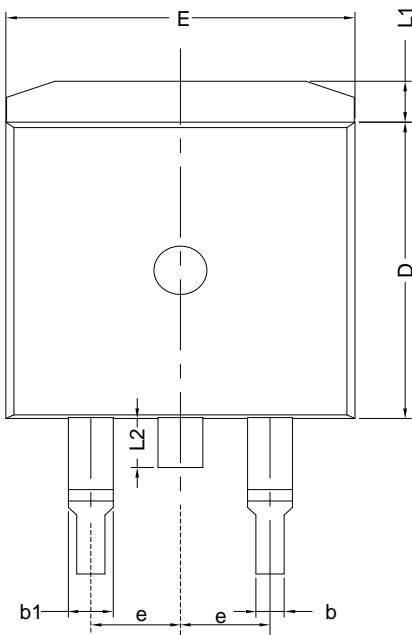








SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	4.30	4.50	4.70
A1	1.00	1.30	1.50
A2	1.80	2.40	2.80
b	0.60	0.80	1.00
b1	1.00	—	1.60
c	0.30	—	0.70
D	15.10	15.70	16.10
D1	8.10	9.20	10.00
E	9.60	9.90	10.40
e	2.54BSC		
H1	6.10	6.50	7.00
L	12.60	13.08	13.60
L1	—	—	3.95
ϕP	3.40	3.70	3.90
Q	2.60	—	3.20



A	4.30	4.57	4.72
A1	0	0	
b	0.71	0.81	0.91
c	0.30		0.60
c2	1.17	1.27	1.37
D	8.50		9.35
E	9.80		10.45
e	2.54BSC		
H	14.70		15.75
L	2.00	2.30	2.74
L1	1.12	1.27	1.42
L2			1.75



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1.3

TRR QRR

1.2

1.1

TO-263-2L

1.0